

# 4V Drive Nch MOS FET

## RSR025N03

**●Structure**

Silicon N-channel  
MOS FET

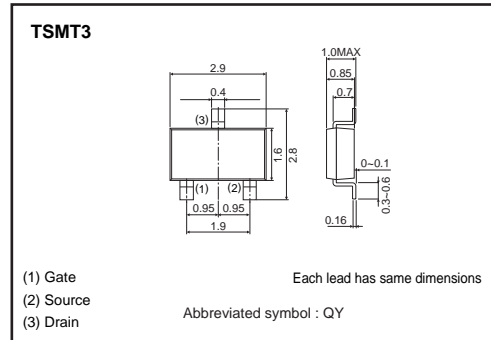
**●Features**

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSM3) .

**●Application**

Power switching, DC / DC converter.

**●External dimensions (Unit : mm)**



**●Packaging specifications**

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSR025N03		○

**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	30	V	
Gate-source voltage	$V_{GSS}$	20	V	
Drain current	Continuous	$I_D$	±2.5	A
	Pulsed	$I_{DP}^{*1}$	±10	A
Source current (Body diode)	Continuous	$I_S$	0.8	A
	Pulsed	$I_{SP}^{*1}$	3.2	A
Total power dissipation	$P_D^{*2}$	1	W	
Channel temperature	$T_{ch}$	150	°C	
Storage temperature	$T_{stg}$	-55 to 150	°C	

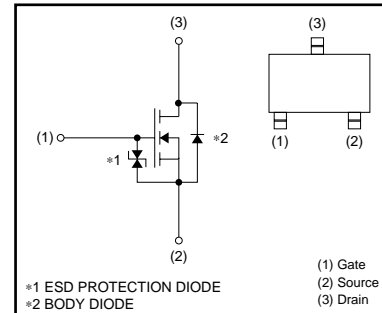
\*1  $P_w \leq 100\mu s$ , Duty cycles  $\leq 2\%$   
\*2 Mounted on a ceramic board.

**●Thermal resistance**

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}^*$	125	°C / W

\*2 Mounted on a ceramic board.

**●Equivalent circuit**



\*1 ESD PROTECTION DIODE  
\*2 BODY DIODE  
\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	10	$\mu A$	$V_{GS}=20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	1	$\mu A$	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	–	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	50	70	m $\Omega$	$I_D=2.5A, V_{GS}=10V$
		–	74	105		$I_D=2.5A, V_{GS}=4.5V$
		–	83	118		$I_D=2.5A, V_{GS}=4V$
Forward transfer admittance	$ Y_{fs} $ *	1.5	–	–	S	$I_D=2.5A, V_{DS}=10V$
Input capacitance	$C_{iss}$	–	165	–	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	–	55	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	35	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	6	–	ns	$I_D=1.25A, V_{DD} \approx 15V$
Rise time	$t_r$ *	–	10	–	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}$ *	–	20	–	ns	$R_L=12.0\Omega$
Fall time	$t_f$ *	–	5	–	ns	$R_G=10\Omega$
Total gate charge	$Q_g$ *	–	2.9	4.1	nC	$V_{DD} \approx 15V$
Gate-source charge	$Q_{gs}$ *	–	0.8	–	nC	$V_{GS}=5V$
Gate-drain charge	$Q_{gd}$ *	–	0.9	–	nC	$I_D=2.5A$

\*Pulsed

## ●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}$ *	–	–	1.2	V	$I_S=3.2A, V_{GS}=0V$

\*Pulsed

Transistors

●Electrical characteristic curves

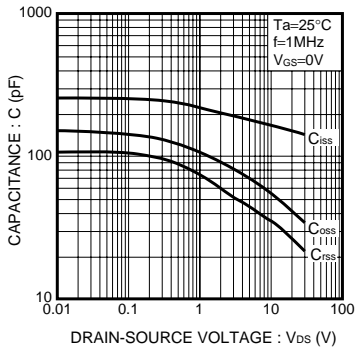


Fig.1 Typical Capacitance vs. Drain-Source Voltage

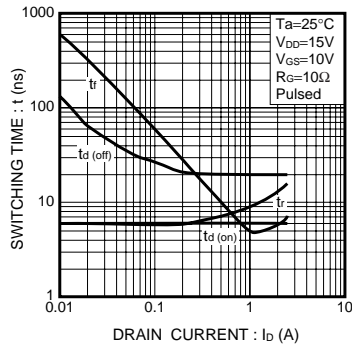


Fig.2 Switching Characteristics

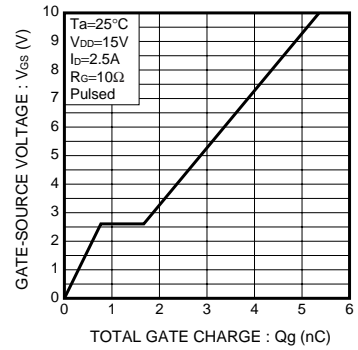


Fig.3 Dynamic Input Characteristics

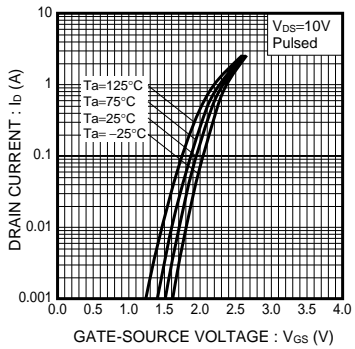


Fig.4 Typical Transfer Characteristics

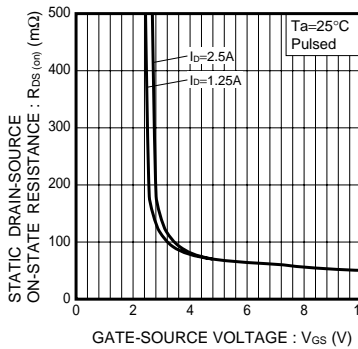


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

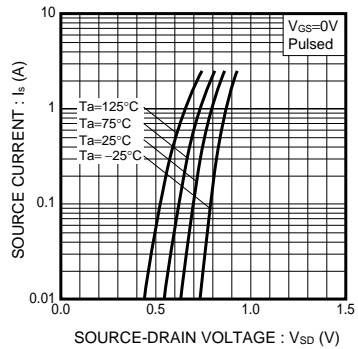


Fig.6 Source Current vs. Source-Drain Voltage

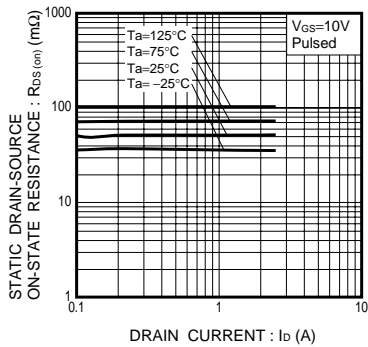


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

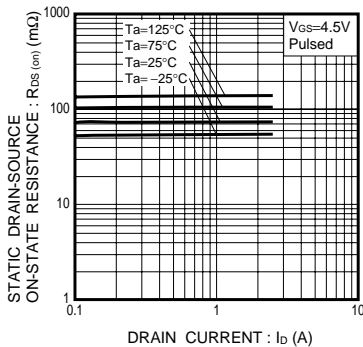


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

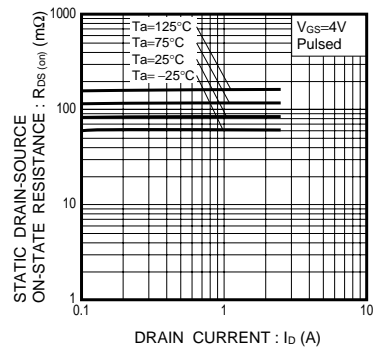


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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